

CONTENTS

Preface	vii
Conference organization	ix
 PART I. METAL-SEMICONDUCTOR INTERFACES	
I-1. CHARACTERIZATION	
From synchrotron radiation to I - V measurements of GaAs Schottky barrier formation W.E. Spicer, R. Cao, K. Miyano, T. Kendelewicz, I. Lindau, E. Weber, Z. Liliental-Weber and N. Newman	1
Ballistic-electron-emission microscopy of subsurface defects at the Au-GaAs(100) interface M.H. Hecht, L.D. Bell and W.J. Kaiser	17
Synchrotron radiation investigation and surface spectroscopy studies of prototypical systems: lead-semiconductor interfaces G. Le Lay, K. Hricovini and J.E. Bonnet	25
Infrared field assisted photoemission of metal-semiconductor structures D. Paget, H.-J. Drouhin and J. Peretti	38
The difference between 6H-SiC (0001) and (000 $\bar{1}$) faces observed by AES, LEED and ESCA S. Nakanishi, H. Tokutaka, K. Nishimori, S. Kishida and N. Ishihara	44
Observation of Si and SiC surface structures using the magnetic LEED method K. Nishimori, H. Tokutaka, Z. Okinaga, S. Kishida and N. Ishihara	49
Characterization of semiconductor oxides by IR diffuse reflectance spectroscopy K. Matsuo and K. Nakano	53
A new non-destructive analysis of semiconductor heterojunctions with very thin surface layers: an application of soft X-ray spectroscopy to Si-compound (film)/Si (substrate) M. Iwami, M. Kusaka, M. Hirai and H. Nakamura	57
 I-2. INITIAL STAGE	
X-ray scattering studies of semiconductor interfaces: atomic structure and morphology E. Vlieg and J.F. van der Veen	62
Initial stages of metal/semiconductor interface formation: Au and Ag on Si(111) R.S. Williams, R.S. Daley, J.H. Huang and R.M. Charatan	70
Photoelectron spectroscopy and photoelectron diffraction studies of Si(001) 2×1 -K and -Cs surfaces S. Kono, Y. Enta, T. Abukawa, T. Kinoshita and T. Sakamoto	75
RHEED intensity analysis of Si(111) $\sqrt{3} \times \sqrt{3}$ -Ag structure A. Ichimiya, S. Kohmoto, T. Fujii and Y. Horio	82
STM studies of metal-semiconductor interface formation F. Salvan, F. Thibaudau and Ph. Dumas	88
Mechanism of alloy formation due to noble metal deposition on silicon surfaces at room temperature: chemical bonding model M. Iwami, M. Kusaka, M. Hirai, M. Kubota, H. Tochiwara and Y. Murata	97
LEED I - V curve analysis for the structure of iron films on Si(111) surfaces T. Urano, M. Kaburagi, S. Hongo and T. Kanaji	103

RHEED intensity analysis of Li/Si(111) structures S. Kohmoto, S. Mizuno and A. Ichimiya	107
Structural study of Ag overlayers deposited on a Si(111) substrate by impact-collision ion-scattering-spectroscopy with time-of-flight detection K. Sumitomo, K. Tanaka, Y. Izawa, I. Katayama, F. Shoji, K. Oura and T. Hanawa	112
Initial stages of aluminum epitaxy on the $\text{Si}(111)\sqrt{3} \times \sqrt{3}$ -Al surface studied by electron-energy-loss spectroscopy S.-T. Li, S. Hasegawa, N. Yamashita and H. Nakashima	118
Application of HREELS to Al/GaAs and Al/GaP interfaces X.M. Ding, G.S. Dong, X.K. Lu, H.Y. Xiao, P. Chen and X. Wang	123
 I-3. SCHOTTKY BARRIER	
Mechanisms of barrier formation in Schottky contacts: metal-induced surface and interface states W. Mönch	128
From heterojunction interfaces to metal-semiconductor interfaces D.W. Niles, M. Tang, J. McKinley, R. Zanoni and G. Margaritondo	139
Semiconductor interface formation: the role of the induced density of interface states F. Flores, A. Muñoz and J.C. Durán	144
Delocalization of defects: a new model for the Schottky barrier R. Ludeke, A. Taleb-Ibrahimi and G. Jezequel	151
Pressure dependences of silicide/silicon Schottky barrier heights J.H. Werner, H. von Känel, G. Markewitz and R.T. Tung	159
Electronic structure of Si/disilicide interfaces H. Fujitani and S. Asano	164
Bismuth on GaAs(110): characterisation of growth mode and Schottky barrier formation at low and room temperature N. Esser, M. Hünemann, U. Resch, D. Spaltmann, J. Geurts, D.R.T. Zahn, W. Richter and R.H. Williams	169
Control of the Al/GaAs Schottky barrier height using a rare-earth metal interlayer K. Hirose, H. Tsuda and T. Mizutani	174
Temperature effects on the formation of the Sb/InP(110) interface D.R.T. Zahn, W. Richter, A.B. McLean, R.H. Williams, C. Stephens, I.T. McGovern, R. Cimino, W. Braun and N. Esser	179
Electrical characteristics of metal contacts on the surfaces of a-Si:H films annealed at low temperature Y. Gekka, M. Saitoh, K. Ohga, Y. Akaida and M. Akimoto	184
 I-4. COMPOUND SEMICONDUCTORS	
Metal contacts to II-VI semiconductors: CdS and CdTe R.H. Williams, N. Forsyth, I.M. Dharmadasa and Z. Sobiesierski	189
Effects of interfacial microstructure on ohmic contacts to GaAs M. Murakami, H.J. Kim, Y.-C. Shih, W.H. Price and C.C. Parks	195
Spectroscopic study of metal/semimetal and metal/semiconductor interfaces R. Sporken, P.A. Thiry, P. Xhonneux, R. Caudano and J.P. Delrue	201
Thermal stability of WSiN-GaAs and Au-WSiN interfaces H. Sugahara and J. Nagano	207
Deep level transient spectroscopic studies of the perovskite oxides as gas sensor material T. Arakawa, H. Baba and G. Adachi	212

Epitaxial growth of a mono-crystalline metastable AuIn layer at the Au/InP(001) interface M. Renda and K. Morita	216
I-5. EPITAXIAL GROWTH	
Epitaxial CoSi ₂ /Si(111) interfaces R.T. Tung and F. Schrey	223
SPA-LEED studies of defects in thin epitaxial NiSi ₂ layers on Si(111) J. Falta, M. Horn and M. Henzler	230
Chemical bonding at metal-semiconductor interfaces P.J. van den Hoek and E.J. Baerends	236
Heteroepitaxy of metallic and semiconducting silicides on silicon N. Cherief, R. Cinti, M. De Crescenzi, J. Derrien, T.A. Nguyen Tan and J.Y. Veuillen	241
Interfacial structure of ICB epitaxially deposited Al(110) bicrystal films on Si(100) substrates I. Yamada	253
Identification of three distinct CoSi ₂ (111)(1 × 1) surface structures L. Haderbache, P. Wetzel, C. Pirri, J.C. Peruchetti, D. Bolmont and G. Gewinner	257
Crystalline quality of heteroepitaxial silicon on epitaxial NiSi ₂ /Si(100) M. Itoh, M. Kinoshita, T. Ajioka, M. Itoh and T. Inada	262
I-6. SILICIDES	
Oxidation of TaSi ₂ thin films on polycrystalline Si T.A. Nguyen Tan, N. Guerfi, J.Y. Veuillen and J. Derrien	266
TiSi ₂ formation at the Ti-rich TiN _x /Si interface N. Fujimura and T. Ito	272
Barrier metal between tungsten and silicon for high temperature processing K. Suguro, Y. Nakasaki, T. Yoshii and T. Itoh	277
Influence of annealing ambients on ZrSi ₂ formation Y. Igarashi, T. Yamaji, S. Nishikawa and S. Ohno	282
Characterization of Si-rich WSi _x on Si N. Fujimura, S. Tachibana and T. Ito	286
Thermal instability of the TiSi ₂ /Si structure: impurity effects S. Ogawa, T. Yoshida, T. Kouzaki, S. Okuda and K. Tsukamoto	290
Interfacial reaction of nickel/hydrogenated amorphous silicon system at low temperature studied by fluorescence EXAFS Y. Kawadzu, M. Iioka, A. Fujii, H. Oyanagi and T. Arai	296
Silicidation of porous silicon and its application for the fabrication of a buried metal layer T. Ito, A. Yamama, A. Hiraki and M. Satou	301
PART II. S/I AND S/S INTERFACES	
II-1. CHARACTERIZATION OF INTERFACE PROPERTIES	
Evaluation of dopant profiles and diffusion constants by means of electron energy loss spectroscopy A. Förster, J.M. Layet and H. Lüth	306
Angle-resolved photoemission study of the As/Ge(100) interface J.F. Morar, U.O. Karlsson, R.I.G. Uhrberg, J. Kanski, P.O. Nilsson and H. Qu	312
Interfacial superstructures studied by grazing incidence X-ray diffraction K. Akimoto, J. Mizuki, I. Hirose and J. Matsui	317

The analysis of complex samples by spectroscopic ellipsometry J.L. Freouf	323
Direct imaging and theoretical modelling of the atomistic morphological and chemical structure of semiconductor heterointerfaces J. Christen, M. Grundmann and D. Bimberg	329
In-situ UHV electron microscope study of metal-silicon surfaces K. Takayanagi, Y. Tanishiro, T. Ishitsuka and K. Akiyama	337
UV absorption spectra of adlayers of MOCVD source gases M. Sasaki, Y. Kawakyu, H. Ishikawa and M. Mashita	342
II-2. I/S INTERFACES	
Bonding at silicon/insulator interfaces F.J. Himpsel, T.F. Heinz, A.B. McLean and E. Palange	346
Local roughness and surface states on Si(001): analysis of vacuum annealings and oxygen adsorption-desorption processes C.A. Sébenne, J.P. Lacharme, I. Andriamanantenaso and M. Khial	352
HRTEM observation of the Si/SiO ₂ interface H. Akatsu and I. Ohdomari	357
The Si(001)/SiO ₂ interface A. Ourmazd, P.H. Fuoss, J. Bevk and J.F. Morar	365
Origin and properties of interface states at insulator-semiconductor and semiconductor-semiconductor interfaces of compound semiconductors H. Hasegawa, H. Ohno, H. Ishii, T. Haga, Y. Abe and H. Takahashi	372
Interface GaAs - gallium fluoride thin film grown by fluorination. Electrical behaviour of the obtained MIS fluorinated GaAs structures A.S. Barrière, G. Couturier, H. Guegan, T. Séguelong, A. Thabti, P. Alnot and J. Chazelas	383
X-ray photo-electron spectroscopy analysis of InP insulator-semiconductor structures prepared by anodic oxidation H. Ishii, H. Hasegawa, A. Ishii and H. Ohno	390
Insulator-semiconductor interface formation by electronic promotion using alkali metal and removal of the catalyst P. Soukiassian, H.I. Starnberg and T. Kendelewicz	395
A computer simulation of the recombination process at compound semiconductor surfaces and hetero-interfaces T. Saitoh, H. Hasegawa, S. Konishi and H. Ohno	402
Optical and interfacial properties of SiO ₂ films deposited on Si by photo-CVD K. Inoue, M. Okuyama and Y. Hamakawa	407
Accumulation of implanted arsenic at the interface during annealing on thermally oxidized Si and SiO ₂ covered Si K. Yokota, K. Ohtsuki, M. Ochi, S. Ishihara and I. Kimura	411
Structural studies of ultrathin silicon oxides and their interfaces by XPS T. Hattori, H. Yamagishi, N. Koike, K. Imai and K. Yamabe	416
Studies on charge trapping and interface state generation in MOS capacitors at low temperatures Y. Yasuda, S. Zaima and M. Sakashita	420
Protuberance growth at polysilicon surfaces during oxidation S. Nadahara, J. Shiozawa, K. Imai, K. Suguro and K. Yamabe	425
Formation of Si-SiO ₂ interfaces at low temperatures using microwave-excited plasma Y. Yasuda, S. Zaima, T. Kaida and Y. Koide	429
Piezoresistance in n-channel inversion layers of Si MOSFET's S. Zaima, T. Maruyama and Y. Yasuda	433

Roughness induced at Si(111) surfaces by high temperature heating Y. Borensztein, T. Lopez-Rios and G. Vuye	439
Surface nitridation of InP with a N ₂ plasma K. Kamimura, Y. Takase, Y. Onuma and A. Kunioka	443
Iron accumulation at the Si-SiO ₂ interface and possible reduction of SiO ₂ Y. Kamiura, F. Hashimoto and M. Iwami	447
 II-3. COMPOUND HETEROINTERFACES	
Heteroepitaxy of a two-dimensional material on a three-dimensional material A. Koma, K. Saiki and Y. Sato	451
Characteristic properties of III-V _A /III-V _B heterointerfaces grown by molecular beam epitaxy M. Yano, M. Ashida, Y. Iwai and M. Inoue	457
Electronic structure of modulation n-doped multiple quantum well C. López, J. Sánchez-Dehesa, F. Meseguer, F. Borondo and K. Ploog	464
RHEED, XPS, HRTEM and channeling studies of molecular beam epitaxy growth of CdTe on (001) GaAs S. Tatarenko, J. Cibert, Y. Gobil, G. Feuillet, K. Saminadayar, A.C. Chami and E. Ligeon	470
Evaluation of disordering at low doping concentration in selectively Si-doped Al _{0.3} Ga _{0.7} As/GaAs heterointerfaces S. Goto, H. Kakibayashi, M. Kawata and T. Usagawa	480
Surface intervalley scattering on GaAs(110) studied with picosecond laser photoemission R. Haight and J.A. Silberman	487
Interface formation on n- and p-CdTe(110) surfaces with Cu and Au B.A. Orlowski, J.P. Lacharme, C.A. Sébenne and S. Bensalah	491
The influence of Cd overpressure in the molecular beam epitaxy of InSb/CdTe heterostructures: a combined Raman and infrared spectroscopy study D.R.T. Zahn, W. Richter, T. Eickhoff, J. Geurts, T.D. Golding, J.H. Dinan, K.J. Mackey and R.H. Williams	497
MOVPE-grown GaN on polar planes of 6H-SiC T. Sasaki, T. Matsuoka and A. Katsui	504
Interface geometry of (GaAs) _n (InAs) _n and (GaP) _n (InP) _n ultra-thin superlattices S.K. De Figueiredo and A.C. Ferraz	509
Characterization of the GaAs buffer layer grown on GaP by MBE for the two-step growth method T. Nomura, K. Wakatuki, M. Miyao and M. Hagino	512
Electrical properties and structures of the MOCVD-AlN/GaAs interface S. Fujieda, K. Akimoto, I. Hirosawa, Y. Mochizuki, J. Mizuki, Y. Matsumoto and J. Matsui	516
Evaluation by resonant light scattering of ZnTe epitaxial layer deposited on GaAs S. Hongo, Y. Kataoka, T. Urano and T. Kanaji	522
Photoluminescence line shape due to arrayed steps at the interfaces of GaAs/AlGaAs single quantum wells grown on vicinal surfaces by molecular beam epitaxy K. Kanamoto, K. Fujiwara, Y. Tokuda, N. Tsukada, M. Ishii and T. Nakayama	526
Raman study of strain distribution in interface region of GaAs/GaP heteroepitaxial layers grown by MBE T. Takeuchi, C. Maezawa, T. Nomura, K. Ishikawa, M. Miyao and M. Hagino	530
Strained-layer superlattice buffers for high-quality heteroepitaxial layers of ZnSe on GaAs S. Hayashi, T. Sakamoto, S. Fujita and S. Fujita	534
Heteroepitaxy between layered semiconductors GaSe and InSe C. Tatsuyama, T. Tanbo and N. Nakayama	539
Charge transport and trapping at the interface in two-layer organic photoconductors Y. Kanemitsu and S. Imamura	544

II-4. SI-BASED INTERFACES

Raman scattering and photoluminescence characterization of Ge/Si strained-layer superlattices grown by phase-locked epitaxy	
H. Okumura, K. Miki, K. Sakamoto, T. Sakamoto, K. Endo and S. Yoshida	548
Distribution of interfacial As atoms in the electron-beam exposure and epitaxy (EBE-epitaxy) technique for growing GaAs films on $\text{CaF}_2/\text{Si}(111)$ structures	
H.C. Lee, H. Ishiwara, S. Furukawa, K. Saiki and A. Koma	553
Chemistry and adhesion of metal-polymer interfaces	
P.S. Ho	559
Atomic rearrangement during the initial stages of GaAs growth on $\text{Si}(111)(\sqrt{3} \times \sqrt{3})$ -Ga surface	
K. Maehashi, S. Hasegawa and H. Nakashima	567
Interfacial structures and selective growth of diamond particles formed by plasma-assisted CVD	
J.-S. Ma, H. Kwarada, T. Yonehara, J.-I. Suzuki, J. Wei, Y. Yokota, H. Mori, H. Fujita and A. Hiraki	572
Formation of a $\text{Ge}_2\text{Si}_{1-x}$ alloy layer by high-energy electron-beam irradiation	
T. Wada, M. Takeda, T. Yamada and M. Ichimura	580
Determination of band line-up in β -SiC/Si heterojunction for Si-HBT's	
T. Aoyama, T. Sugi and T. Ito	584
Raman study of the stress in MBE-grown $\text{Al}_x\text{Ga}_{1-x}\text{As}$ on Si	
K. Iizuka, T. Yoshida, M. Hasobe, I. Matsuda and T. Suzuki	587
Properties of a-Si:H based interface transient layers measured by in-situ ellipsometry	
Y. Hatanaka, K. Mitsuoka and T. Yamaguchi	591
Interfacial layers of InP/Si heteroepitaxy	
H. Horikawa, M. Akiyama, S. Onozawa, Y. Kawai and M. Sakuta	598
Porous silicon: the material and its applications in silicon-on-insulator technologies	
G. Bomchil, A. Halimaoui and R. Herino	604
Low temperature oxidation of crystalline porous silicon	
Y. Kato, T. Ito and A. Hiraki	614
Crystal-amorphous-silicon interface kinetics under ion beam irradiation	
F. Priolo, A. La Ferla, C. Spinella, E. Rimini, S.U. Campisano and G. Ferla	619

II-5. SOS AND SOI

Applications of the silicon wafer direct-bonding technique to electron devices	
K. Furukawa and A. Nakagawa	627
Growth behavior of highly oriented Si films on fused quartz by photo-CVD	
M. Okuyama, N. Fujiki, Y. Nakatani, K. Inoue and Y. Hamakawa	633
Selective nucleation based epitaxy (Sentaxy). Investigation of initial nucleation stages	
H. Kumomi, T. Yonehara, Y. Nishigaki and N. Sato	638
Microstructure of high temperature annealed SIMOX wafer	
H. Miyatake, Y. Yamaguchi, Y. Mashiko, T. Nishimura and H. Koyama	643
Photoemission studies of bonding properties at the MBE-grown CaF_2/GaAs interface	
Y. Yamada Maruo, M. Oshima, T. Waho, T. Kawamura, S. Maeyama and T. Miyahara	647
Author index	654
Subject index	662

